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DN0150ALP4 / DN0150BLP4

50V NPN SMALL SIGNAL TRANSISTOR IN DFN1006

Features

- BV_{CEO} > 50V
- I_C = 100mA High Collector Current
- P_D = 1000mW Power Dissipation
- 0.60mm² Package Footprint, 13 times Smaller than SOT23
- 0.4mm Height Package Minimizing Off-Board Profile
- Complementary PNP Type: DP0150ALP4/DP0150BLP4
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

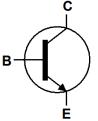
Mechanical Data

- Case: X2-DFN1006-3
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020 Terminals: Finish — NiPdAu.
- Solderable per MIL-STD-202, Method 208@4
- Weight: 0.0008 grams (Approximate)

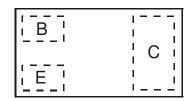
X2-DFN1006-3







Device Symbol



Top View Pin Configuration

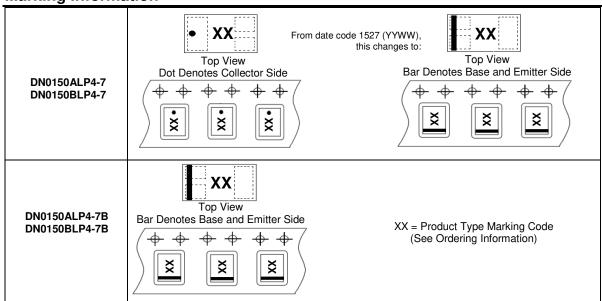
Ordering Information (Note 4)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DN0150ALP4-7	T3	7	8	3,000
DN0150ALP4-7B	Т3	7	8	10,000
DN0150BLP4-7	T4	7	8	3,000
DN0150BLP4-7B	T4	7	8	10,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information





Absolute Maximum Ratings (@ $T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V _{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current – Continuous	lc	100	mA
Peak Pulse Collector Current	Ісм	200	mA
Base Current	Ι _Β	30	mA

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)	D-	400	- mW	
Power Dissipation	(Note 6)	P _D	1000		
Thermal Pagistance, Junation to Ambient	(Note 5)	D	310	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{ hetaJA}$	120	- C/VV	
Thermal Resistance, Junction to Lead (Note 7)		$R_{ heta JL}$	120	°C/W	
Operating and Storage and Temperature Range	T _J , T _{STG}	-55 to +150	°C		

ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

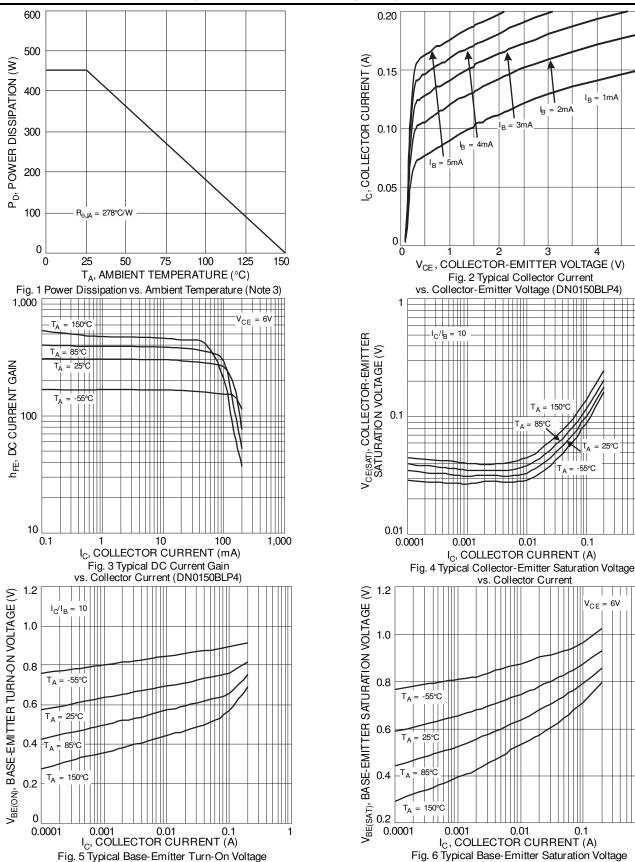
Characteristic		Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS							
Collector-Base Breakdown Voltage		BV _{CBO}	60	_	_	V	$I_C = 10\mu A, I_E = 0$
Collector-Emitter Breakdown Volt	age (Note 8)	BV _{CEO}	50	_	_	V	$I_C = 1 \text{mA}, I_B = 0$
Emitter-Base Breakdown Voltage		BV _{EBO}	5	_	_	V	$I_E = 10\mu A, I_C = 0$
Collector Cut-Off Current		I _{CBO}	_	_	0.1	μΑ	$V_{CB} = 60V, I_{E} = 0$
Emitter Cut-Off Current		I _{EBO}	_	_	0.1	μΑ	$V_{EB} = 5V, I_{C} = 0$
ON CHARACTERISTICS (Note 9	9)	•					•
Collector-Emitter Saturation Volta	ige	V _{CE(SAT)}	_	0.10	0.25	V	$I_C = 100 \text{mA}, I_B = 10 \text{mA}$
DC Current Gain DN0150ALP4 DN0150BLP4		h _{FE}	120 200		240 400	_	$V_{CE} = 6V$, $I_C = 2mA$
SMALL SIGNAL CHARACTERIS	STICS	•					•
Transition Frequency		f _T	60	_	_	MHz	$V_{CE} = 10V, I_{E} = -1mA$ f = 30MHz
Output Capacitance		C _{ob}	_	1.3	_	pF	$V_{CB} = 10V, I_E = 0,$ f = 1MHz

Notes:

- 5. For the device mounted on minimum recommended pad layout 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady state condition. The entire exposed collector pad is attached to the heatsink.
- 6. Same as Note 5, except the exposed collector pad is mounted on 25mm x 25mm 2oz copper.
- 7. Thermal resistance from junction to solder-point (on the exposed collector pad).
- 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.
- Measured under pulsed conditions. Pulse width ≤ 300µs. Duty cycle ≤ 2%.



Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



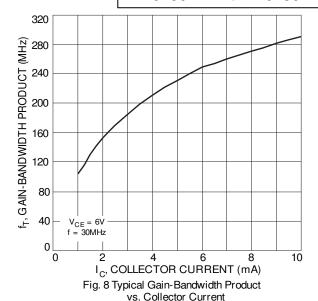
vs. Collector Current

vs. Collector Current



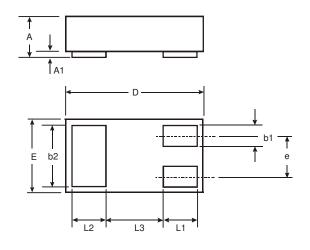
Fig. 7 Typical Capacitance Characteristics

DN0150ALP4 / DN0150BLP4



Package Outline Dimensions

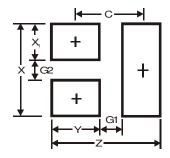
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



X2-DFN1006-3					
Dim	Min	Max	Тур		
Α	_	0.40	_		
A1	0	0.05	0.02		
b1	0.10	0.20	0.15		
b2	0.45	0.55	0.50		
D	0.95	1.05	1.00		
Е	0.55	0.65	0.60		
е	_	_	0.35		
L1	0.20	0.30	0.25		
L2	0.20	0.30	0.25		
L3			0.40		
All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	1.1
G1	0.3
G2	0.2
Х	0.7
X1	0.25
Υ	0.4
С	0.7



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